

Optical module electrical chip gesi



Overview

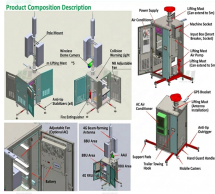
Model and simulate a Germanium-Silicon (GeSi) electro-absorption modulator (EAM) on Silicon-on-insulator (SOI). The eigenmode expansion (EME) and CHARGE solvers are used to simulate the modul.



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he proposed transceiver does pose several drawback in terms of cost, power and footprint, when envisioned as a device for short-reach optical interconnects. Two co-packaged InP-based electrical ...



One of the main building blocks of this technology is the GeSi Electro-Absorption Modulator (EAM). These devices exploit the Franz-Keldysh (FK) effect in epitaxially grown GeSi or Ge, to enable high ...



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In this paper, we demonstrate the first silicon-based EAM, in combination with an in-house developed SiGe BiCMOS transceiver chipset, capable of transmitting single-lane 100 Gb/s...



r ongoing work on compact and low-power GeSi EA modulators for 100G serial optical interconnects. We were able to demonstrate the first silicon-based modulators capable of transmitting 100 Gb/s ...



230-Gb/s on-chip optical interconnection is experimentally demonstrated using GeSi electro-absorption modulator and photodetector. The demonstrated results indicate that GeSi-based ...



In this review, we discuss the current state of knowledge and the on-going challenges concerning the development of high performance GeSi electro-absorption modulators. We also provide feasible ...



The demonstrated results indicate that GeSi-based integration transceiver chip are promising solutions for low cost and high-speed on-chip optical interconnection.



The invention relates to the field of optical modulators, and in particular to a high speed and low loss GeSi/Si electro-absorption light modulator. Si-based modulators are highly required...



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Contact Us

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